

**IN THE CLAIMS:**

**Amendments to the Claims**

Please cancel claims 1-12, 14, 16-34 and 37-64 without prejudice or disclaimer of the subject matter thereof, without prejudice to the right to file a divisional application with respect to claims 30, 37-49 and 54 which stand withdrawn from consideration, and add the new claims as shown below.

**Listing of Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

Claims 1-66 (canceled)

67. (new) A plasma etching apparatus comprising:  
a vacuum chamber;  
vacuum generating means;  
a sample stage installed in the vacuum chamber for holding a sample thereon;  
a planar plate disposed in parallel with the sample stage in the vacuum chamber;  
means for generating plasma in a space between the sample stage and the planar plate including electromagnetic wave supply means and magnetic field generating means;  
a first power source for applying a bias to the planar plate;  
a second power source for applying a bias to the sample stage;

gas supply means for supplying a source material gas into the plasma generated in the vacuum chamber;

wherein the planar plate includes a plurality of holes, and the source material gas is supplied through the plurality of holes; and

wherein a distance between the planar plate and the sample held on the sample stage is in a range from 30 mm to one half of the smaller of one of a diameter of the sample and a diameter of the planar plate.

68. (new) A plasma etching apparatus according to claim 67, further comprising a ring-shaped member disposed at a periphery of the sample stage, wherein the second power source is connected to the ring-shaped member.

69. (new) A plasma etching apparatus according to claim 67, further comprising means for control of temperature of the ring-shaped member.

70. (new) A plasma etching apparatus according to claim 67, wherein the electromagnetic wave supply means to generate the plasma provides an electromagnetic wave having a frequency ranging from 300 MHz to 500 MHz.

71. (new) A plasma etching apparatus according to claim 67, wherein the ring-shaped member includes a surface to be brought into contact with the plasma, the surface being made of one of silicon, carbon, silicon carbide, quartz, aluminum oxide, and aluminum.

72. (new) A plasma etching apparatus according to claim 68, further comprising means for dividing a power from the second power source, the dividing means being configured so as to divide high frequency power from the second

power source into one part for the sample stage and another part for the ring-shaped member.